

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **UFT30-28** is Designed for Class A and B Power Amplifiers Operating up to 500 MHz.

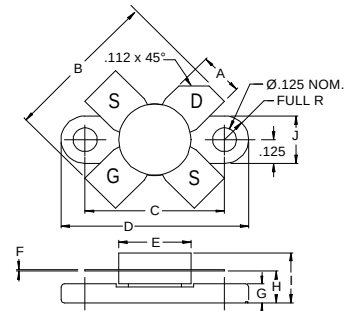
FEATURES:

- $P_G = 7.0$ dB min. at 25 W/400 MHz
- $\eta_D = 60$ % Typical
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_D	5.0 A
V_{DDS}	65 V
V_{GS}	± 40 V
P_{DISS}	100 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{1C}	1.8 $^\circ\text{C/W}$

PACKAGE STYLE .380 4L FLG.



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10666

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{DSS}	$I_{DS} = 10$ mA		60			V
I_{DSS}	$V_{DS} = 28$ V				4.0	mA
I_{GSS}	$V_{GS} = 20$ V				1.0	μA
V_{GS}	$V_{DS} = 10$ V	$I_D = 25$ mA	1.0		6.0	V
G_{FS}	$V_{DS} = 10$ V	$I_D = 500$ mA	500			mMho
C_{ISS} C_{OSS} C_{RSS}	$V_{DS} = 28$ V	$V_{GS} = 0$ V	$f = 1.0$ MHz		46 33 6.0	pF
P_G η_D	$V_{DD} = 28$ V $f = 400$ MHz	$I_{DQ} = 25$ mA $P_{OUT} = 25$ W	7.0 60			dB %